

PSMN022-30PL

N-channel 30 V 22 mΩ logic level MOSFET Rev. 02 — 1 November 2010

Product data sheet

Product profile 1.

1.1 General description

Logic level N-channel MOSFET in TO220 package qualified to 175 °C. This product is designed and qualified for use in a wide range of industrial, communications and domestic equipment.

1.2 Features and benefits

- High efficiency due to low switching and conduction losses
- Suitable for logic level gate drive sources

1.3 Applications

- DC-to-DC converters
- Load switching

- Motor control
- Server power supplies

1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
-				. , P		
V _{DS}	drain-source voltage	$T_j \ge 25 \text{ °C}; T_j \le 175 \text{ °C}$	-	-	30	V
I _D	drain current	T_{mb} = 25 °C; V_{GS} = 10 V; see <u>Figure 1</u>	-	-	30	Α
P_{tot}	total power dissipation	T _{mb} = 25 °C; see <u>Figure 2</u>	-	-	41	W
T _j	junction temperature		-55	-	175	°C
Static chara	acteristics					
R_{DSon}	drain-source on-state resistance	$V_{GS} = 4.5 \text{ V}; I_D = 5 \text{ A};$ $T_j = 25 ^{\circ}\text{C}; \text{ see } \frac{\text{Figure } 13}{\text{ Figure } 13}$	-	27	34	mΩ
		$V_{GS} = 10 \text{ V; } I_D = 5 \text{ A;}$ $T_j = 25 \text{ °C; see } \frac{\text{Figure } 13}{}$	-	19	22	mΩ
Dynamic cl	naracteristics					
Q_{GD}	gate-drain charge	$V_{GS} = 4.5 \text{ V}; I_D = 5 \text{ A};$	-	1.4	-	nC
Q _{G(tot)}	total gate charge	V _{DS} = 15 V; see <u>Figure 14</u> ; see <u>Figure 15</u>	-	4.4	-	nC
Avalanche	ruggedness					
E _{DS(AL)S}	non-repetitive drain-source avalanche energy	V_{GS} = 10 V; $T_{j(init)}$ = 25 °C; I_D = 30 A; V_{sup} ≤ 30 V; R_{GS} = 50 Ω ; unclamped	-	-	7	mJ



2. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate		
2	D	drain	mb	D
3	S	source		_G (EA)
mb	D	mounting base; connected to drain	1 2 3	mbb076 S
			SOT78 (TO-220AB)	

3. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
PSMN022-30PL	TO-220AB	plastic single-ended package; heatsink mounted; 1 mounting hole; 3-lead TO-220AB	SOT78

4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 175 °C	-	30	V
V_{DGR}	drain-gate voltage	$T_j \ge 25 \text{ °C}; T_j \le 175 \text{ °C}; R_{GS} = 20 \text{ k}\Omega$	-	30	V
V_{GS}	gate-source voltage		-20	20	V
I _D	drain current	$V_{GS} = 10 \text{ V; } T_{mb} = 100 \text{ °C; see } \frac{\text{Figure 1}}{}$	-	22	Α
		$V_{GS} = 10 \text{ V; } T_{mb} = 25 \text{ °C; see } \underline{\text{Figure 1}}$	-	30	Α
I _{DM}	peak drain current	pulsed; $t_p \le 10 \mu s$; $T_{mb} = 25 \text{ °C}$; see Figure 3	-	125	Α
P _{tot}	total power dissipation	T _{mb} = 25 °C; see <u>Figure 2</u>	-	41	W
T _{stg}	storage temperature		-55	175	°C
Tj	junction temperature		-55	175	°C
Source-drain	diode				
Is	source current	T _{mb} = 25 °C	-	30	Α
I _{SM}	peak source current	pulsed; $t_p \le 10 \ \mu s$; $T_{mb} = 25 \ ^{\circ}C$	-	125	Α
Avalanche ruggedness					
E _{DS(AL)S}	non-repetitive drain-source avalanche energy	V_{GS} = 10 V; $T_{j(init)}$ = 25 °C; I_D = 30 A; V_{sup} ≤ 30 V; R_{GS} = 50 Ω ; unclamped	-	7	mJ

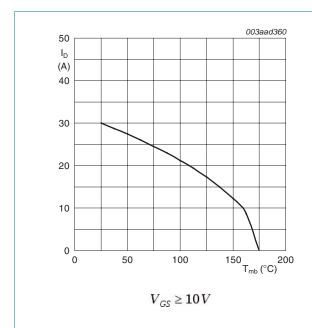
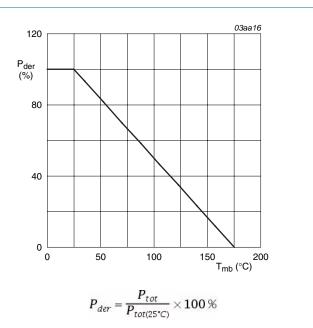
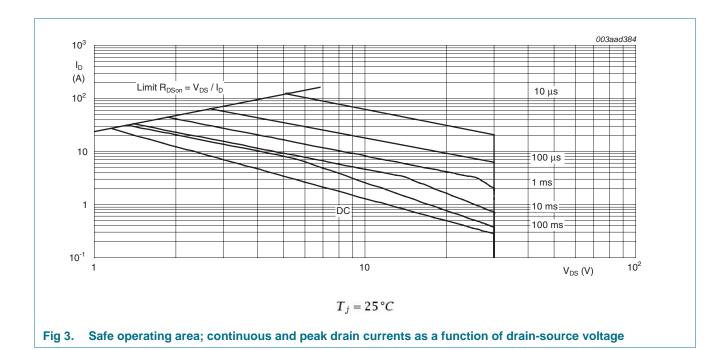


Fig 1. Continuous drain current as a function of mounting base temperature



2. Normalized total power dissipation as a function of mounting base temperature



5. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	see Figure 4	-	3.1	3.6	K/W

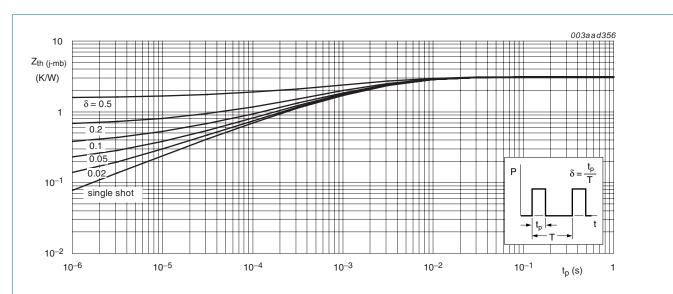


Fig 4. Transient thermal impedance from junction to mounting base as a function of pulse duration; typical values

6. Characteristics

Table 6. Characteristics

Table 6.	Characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static cha	aracteristics					
$V_{(BR)DSS}$	drain-source breakdown	$I_D = 250 \mu A; V_{GS} = 0 V; T_j = 25 °C$	30	-	-	V
	voltage	$I_D = 250 \mu A; V_{GS} = 0 V; T_j = -55 °C$	27	-	-	V
$V_{GS(th)}$	gate-source threshold voltage	$I_D = 1 \text{ mA}$; $V_{DS} = V_{GS}$; $T_j = 25 \text{ °C}$; see <u>Figure 10</u> ; see <u>Figure 11</u>	1.3	1.7	2.15	V
		$I_D = 1 \text{ mA}$; $V_{DS} = V_{GS}$; $T_j = 175 \text{ °C}$; see Figure 11	0.5	-	-	V
		$I_D = 1 \text{ mA}$; $V_{DS} = V_{GS}$; $T_j = -55 \text{ °C}$; see Figure 11	-	-	2.45	V
I_{DSS}	drain leakage current	$V_{DS} = 30 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	0.3	1	μΑ
		$V_{DS} = 30 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 125 \text{ °C}$	-	-	50	μΑ
I_{GSS}	gate leakage current	$V_{GS} = 16 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	10	100	nA
		$V_{GS} = -16 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	10	100	nA
R_{DSon}	drain-source on-state resistance	$V_{GS} = 4.5 \text{ V}; I_D = 5 \text{ A}; T_j = 175 ^{\circ}\text{C};$ see Figure 12	-	-	64.6	mΩ
		$V_{GS} = 4.5 \text{ V}; I_D = 5 \text{ A}; T_j = 25 ^{\circ}\text{C};$ see Figure 13	-	27	34	mΩ
		$V_{GS} = 10 \text{ V}; I_D = 5 \text{ A}; T_j = 175 °C;$ see Figure 12	-	35	41.8	mΩ
		$V_{GS} = 10 \text{ V}; I_D = 5 \text{ A}; T_j = 100 °C;$ see Figure 12	-	-	31	mΩ
		$V_{GS} = 10 \text{ V; } I_D = 5 \text{ A; } T_j = 25 \text{ °C;}$ see Figure 13	-	19	22	mΩ
R_{G}	gate resistance	f = 1 MHz	-	2	-	Ω
Dynamic	characteristics					
Q _{G(tot)}	total gate charge	$I_D = 5 \text{ A}$; $V_{DS} = 15 \text{ V}$; $V_{GS} = 10 \text{ V}$; see Figure 14; see Figure 15	-	9	-	nC
		$I_D = 0 \text{ A}; V_{DS} = 0 \text{ V}; V_{GS} = 10 \text{ V}$	-	8	-	nC
		$I_D = 5 A$; $V_{DS} = 15 V$; $V_{GS} = 4.5 V$;	-	4.4	-	nC
Q_{GS}	gate-source charge	see Figure 14; see Figure 15	-	1.6	-	nC
Q _{GS(th)}	pre-threshold gate-source charge	$I_D = 5 \text{ A}$; $V_{DS} = 15 \text{ V}$; $V_{GS} = 4.5 \text{ V}$; see Figure 14	-	0.8	-	nC
Q _{GS(th-pl)}	post-threshold gate-source charge		-	0.8	-	nC
Q_{GD}	gate-drain charge	$I_D = 5 \text{ A}$; $V_{DS} = 15 \text{ V}$; $V_{GS} = 4.5 \text{ V}$; see Figure 14; see Figure 15	-	1.4	-	nC
$V_{GS(pl)}$	gate-source plateau voltage	V _{DS} = 15 V; see <u>Figure 14</u> ; see <u>Figure 15</u>	-	3	-	V
C _{iss}	input capacitance	$V_{DS} = 15 \text{ V}; V_{GS} = 0 \text{ V}; f = 1 \text{ MHz};$	-	447	-	pF
C _{oss}	output capacitance	T _j = 25 °C; see <u>Figure 16</u>	-	96	-	pF
C _{rss}	reverse transfer capacitance		-	61	-	pF

 Table 6.
 Characteristics ...continued

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$t_{d(on)}$	turn-on delay time	$V_{DS} = 15 \text{ V}; R_L = 1.5 \Omega; V_{GS} = 4.5 \text{ V};$	-	12	-	ns
t _r	rise time	$R_{G(ext)} = 4.7 \Omega$	-	29	-	ns
t _{d(off)}	turn-off delay time		-	17	-	ns
t _f	fall time		-	7	-	ns
Source-dra	in diode					
V_{SD}	source-drain voltage	$I_S = 5 \text{ A}$; $V_{GS} = 0 \text{ V}$; $T_j = 25 \text{ °C}$; see <u>Figure 17</u>	-	0.7	1.2	V
t _{rr}	reverse recovery time	$I_S = 5 \text{ A}$; $dI_S/dt = -100 \text{ A/}\mu\text{s}$;	-	22	-	ns
Q _r	recovered charge	$V_{GS} = 0 \text{ V}; V_{DS} = 20 \text{ V}$	-	10	-	nC

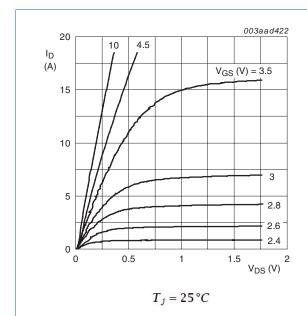


Fig 5. Output characteristics: drain current as a function of drain-source voltage; typical values

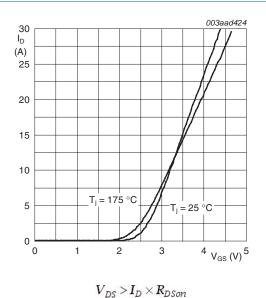


Fig 6. Transfer characteristics: drain current as a function of gate-source voltage; typical values

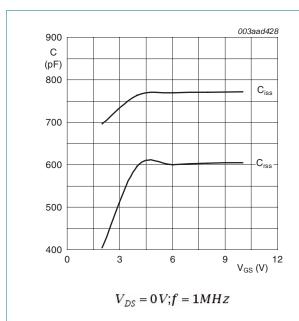


Fig 7. Input and reverse transfer capacitances as a function of gate-source voltage; typical values

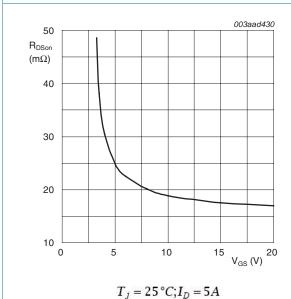


Fig 9. Drain-source on-state resistance as a function of gate-source voltage; typical values

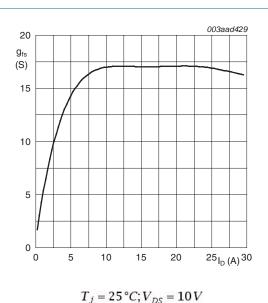
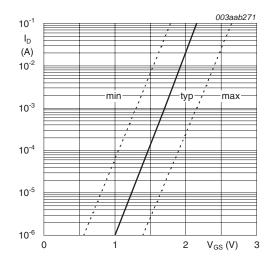


Fig 8. Forward transconductance as a function of drain current; typical values



 $T_j = 25 \,{}^{\circ}C; V_{DS} = 5V$

Fig 10. Sub-threshold drain current as a function of gate-source voltage

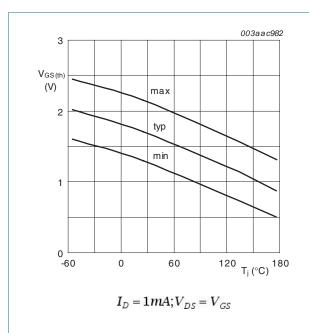


Fig 11. Gate-source threshold voltage as a function of junction temperature

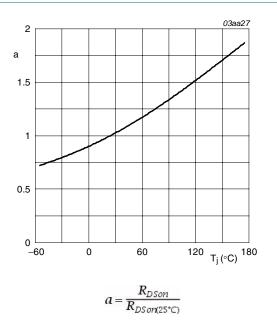


Fig 12. Normalized drain-source on-state resistance factor as a function of junction temperature

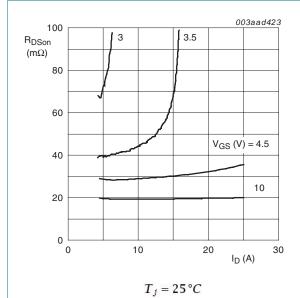


Fig 13. Drain-source on-state resistance as a function of drain current; typical values

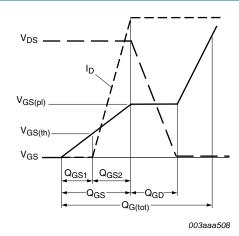


Fig 14. Gate charge waveform definitions

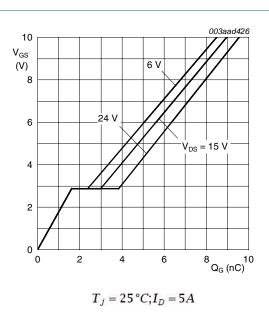
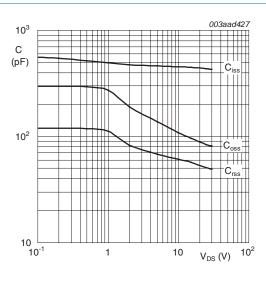


Fig 15. Gate-source voltage as a function of gate charge; typical values



 $V_{GS} = 0V; f = 1MHz$

Fig 16. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

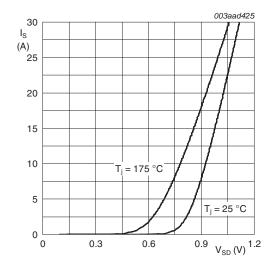
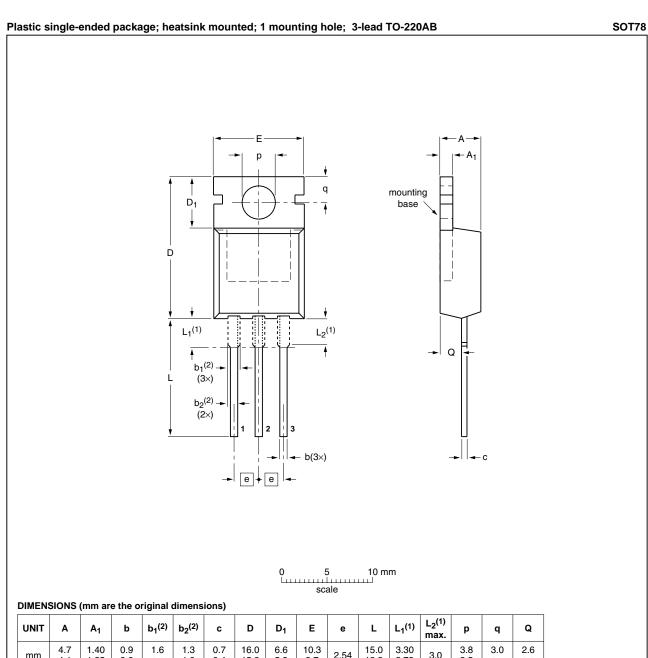


Fig 17. Source (diode forward) current as a function of source-drain (diode forward) voltage; typical values

 $V_{GS} = 0V$

Package outline



UNIT	А	A ₁	b	b ₁ (2)	b ₂ (2)	С	D	D ₁	E	е	L	L ₁ (1)	L ₂ ⁽¹⁾ max.	р	q	Q
mm	4.7 4.1	1.40 1.25	0.9 0.6	1.6 1.0	1.3 1.0	0.7 0.4	16.0 15.2	6.6 5.9	10.3 9.7	2.54	15.0 12.8	3.30 2.79	3.0	3.8 3.5	3.0 2.7	2.6 2.2

- 1. Lead shoulder designs may vary.
- 2. Dimension includes excess dambar.

OUTLINE		REFER	ENCES	EUROPEAN	ISSUE DATE
VERSION	IEC	JEDEC	JEITA	PROJECTION	ISSUE DATE
SOT78		3-lead TO-220AB	SC-46		08-04-23 08-06-13

Fig 18. Package outline SOT78 (TO-220AB)

PSMN022-30PL

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8. Revision history

Table 7. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
PSMN022-30PL v.2	20101101	Product data sheet	-	PSMN022-30PL v.1
Modifications:	 Various change 	es to content.		
PSMN022-30PL v.1	20101018	Product data sheet	-	-

9. Legal information

9.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions"
- [3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL http://www.nexperia.com.

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PSMN022-30PL

Nexperia

N-channel 30 V 22 mΩ logic level MOSFET

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